

T879N SERIES

DISC TYPE THYRISTOR

Features

- Center amplifying gate
- Metal case with ceramic insulator
- tested according to IEC standards

879A

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	T879N	Units
I _{T(AV)}	879	A
	@ T _{hs}	°C
I _{T(RMS)}	1440	A
	@ T _{hs}	°C
I _{TSM}	7850	A
	@ 60Hz	8220
I ² t	@ 50Hz	308
	@ 60Hz	281
V _{DRM} / V _{RRM}	1800	V
T _q typical	150	μs
T _J range	- 40 to 125	°C

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ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non- repetitive peak rev. voltage V	I_{RRM} max. @ $T_J = 125^\circ\text{C}$ mA
T879N	10	1000	1100	20
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	

On-state Conduction

Parameter	T879N	Units	Conditions				
$I_{(AV)}$ Maximum average on-state current @ Heatsink temperature	879	A	180° conduction, half sine wave	No voltage reapplied			
	55	°C					
$I_{(RMS)}$ Maximum RMS on-state current	1440	A	DC@ 25°C heatsink temperature double side cooled				
I_{TSM} , Maximum peak, one-cycle non-repetitive surge current	7850	A	$t = 10\text{ms}$	100% V_{RRM} reapplied	Sinusoidal half wave, Initial T = T max.		
	8220		$t = 8.3\text{ms}$				
	6600		$t = 10\text{ms}$				
	6900		$t = 8.3\text{ms}$				
$I^2 t$ Maximum $I^2 t$ for fusing	308	KA ² s	$t = 10\text{ms}$	No voltage reapplied			
	281		$t = 8.3\text{ms}$				
	218		$t = 10\text{ms}$				
	200		$t = 8.3\text{ms}$				
$I^2 \sqrt{t}$ Maximum $I^2 \sqrt{t}$ for fusing	3080	KA ² √ s	$t = 0.1$ to 10ms, no voltage reapplied				
V_{TM} Maximum on-state or forward	1.36	V	$I_{pk} = 105\text{A}$, $T_J = 125^\circ\text{C}$, $t_p = 10\text{ms}$ sine pulse				
I_H Maximum holding current	600	mA	$T_J = 25^\circ\text{C}$, anode supply 12V resistive load				
I_L Typical latching current	1000						

Switching

Parameter	T879N	Units	Conditions	
di/dt Maximum non repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu\text{s}$ $T_J = T_{J\max}$, anode voltage $\leq 80\%$ V_{DRM}	
td Typical delay time	1.0	μs		
Tq Typical turn-off time	150	A/μs	Gate current 1A, di/dt = 1A/μs $V_d = 0.67\%$ V_{DRM} , $T_J = 25^\circ\text{C}$	
			$I_{TM} = 300\text{A}$, $T_J = T_{J\max}$, di/dt = 20A/μs, $V_R = 50\text{V}$ $dv/dt = 20\text{V}/\mu\text{s}$, Gate 0V 100Ω, $t_p = 500\mu\text{s}$	

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Blocking

Parameter	T879N	Unit s	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	T _J = T _J max linear to 80% rated V _{DRM}
I _{DRM} Max. peak reverse and off-state leakage current	30	mA	T _J = T _J max, rated V _{DRM} /V _{RRM} applied

Triggering

Parameter	T879N		Units	Conditions
P _{GM} Maximum peak gate power	10	W	T _J = T _J max, t _p ≤ 5ms	
P _{G(AV)} Maximum average gate power	2.0		T _J = T _J max, f = 50Hz, d% = 50	
I _{GM} Max. peak positive gate current	3.0	A	T _J = T _J max, t _p ≤ 5ms	
+V _{GM} Maximum peak positive gate voltage	20	V		
-V _{GM} Maximum peak negative gate voltage	5.0		T _J = T _J max, t _p ≤ 5ms	
I _{GT} DC gate current required to trigger	TYP. 180 90 40	MAX. - 150 -	mA	T _J = -40°C T _J = 25°C T _J = 125°C Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
V _{GT} DC gate voltage required to trigger	2.9 1.8 1.2	- 30 -		
I _{GD} DC gate current not to trigger	10	mA	T _J = T _J max	Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated V anode-to-cathode applied
V _{GD} DC gate voltage not to trigger	0.30	V		

Thermal and Mechanical Specification

Parameter	T879N	Units	Conditions
T _J Max. operating temperature range	-40 to 125	°C	
T _{stg} Max. storage temperature range	-40 to 150		
R _{thJC} Max. thermal resistance, junction to case	0.17 0.08	K/W	DC operation
R _{thCS} Max. thermal resistance, case to heatsink	0.033 0.017		Mounting surface, smooth, flat and greased
T Mounting torque, ± 10%	4900 (500)		
wt Approximate weight	260	g	

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Outline Table

